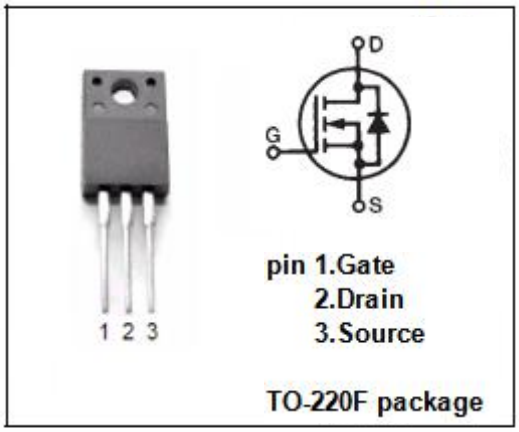
iscN-Channel MOSFET Transistor IRFIBC40GLC

- **FEATURES**
- Low drain-source on-resistance:
  R_{DS}(ON) = 1.2Ω (MAX)
- Enhancement mode:
  Vth = 2 to 4V (V_{DS} = 10 V, I_D=0.25mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



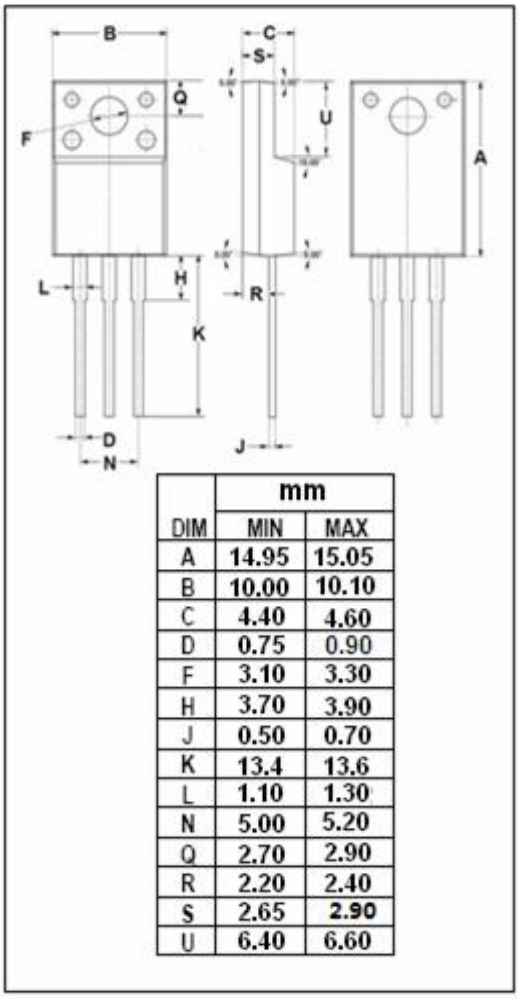
- **DESCRITION**
- Switching Voltage Regulators

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	3.5	A
I_{DM}	Drain Current-Single Pulsed	14	A
P_D	Total Dissipation @T_C=25℃	40	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.1	℃/W



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D=0.25mA	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V; I_D= 2.1A			1.2	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V; V_{GS}= 0V V_{DS}=480V; V_{GS}= 0V; T_J=125℃			25 250	μA
V_{SDF}	Diode forward voltage	I_{DR} =3.5A, V_{GS} = 0 V			1.5	V